

consisting of $C(CH_2OH)_3$, a sugar unit, SiR_3 wherein R is a polar group selected from the group consisting of:

65. The method according to Claim 34, wherein the composition
5 further comprises a co-solvent.

66. The method according to Claim 34, further comprising the step
of selectively etching the wafer, wherein said step of selectively etching the
wafer occurs subsequent to step (c) but prior to step (d).

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67. A process of forming integrated circuits comprising the steps of:

(a) inserting at least one wafer into an integrated microelectronics
process device (IMPD); then

(b) contacting the at least one wafer with a first composition
15 comprising a component selected from the group consisting of at least one
polymeric material, at least one polymeric precursor, and at least one
monomer, and mixtures thereof, to deposit the component on the substrate
and form a coating thereon; then

(c) imagewise exposing the coating to radiation such that exposed
20 and unexposed coating portions are formed; then

(d) subjecting the coating to a second composition comprising
carbon dioxide such that either one of the exposed or the unexposed coating
portions are removed from the at least one wafer and the other coating portion
is developed and remains on the coating to form an image thereon; then

(e) depositing a metal-containing material or an ionic material on
25 the surface of the wafer from which the exposed or the unexposed coating
portions are removed; then

(f) removing the exposed or unexposed coating portion from the
substrate; and then

(g) removing the at least one wafer from the IMPD;
30 wherein said steps (a) through (f) are performed in an IMPD without the
at least one wafer being removed from the IMPD.